VS-HFA08TB60SPbF

Vishay Semiconductors

RoHS COMPLIANT

HALOGEN

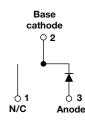
FREE

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



www.vishay.com

TO-263AB (D²PAK)



PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
I _{F(AV)}	8 A						
V _R	600 V						
V _F at I _F	1.4 V						
t _{rr} (typ.)	18 ns						
T _J max.	150 °C						
Diode variation	Single die						

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TB60S is ideally suited for applications in power supplies (PFC boost diode) and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward current	I _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		60	А					
Maximum repetitive forward current	I _{FRM}		24						
Maximum power dissipation	D-	T _C = 25 °C	36	W					
Maximum power dissipation	PD	T _C = 100 °C	14	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
Maximum forward voltage		I _F = 8.0 A		-	1.4	1.7	v		
	V_{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1			
		I _F = 8.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse		$V_{\rm R} = V_{\rm R}$ rated	See fig. 2	-	0.3	5.0			
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	100	500	μΑ		
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	ackage body	-	8.0	-	nH		

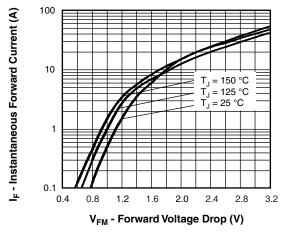
DYNAMIC RECOVERY CHARACTERISTICS (TJ = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time See fig. 5, 6	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/µs, V _R = 30 V	-	18	-			
	t _{rr1}	T _J = 25 °C		-	37	55	ns		
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	55	90			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	3.5	5.0	- A - nC		
	I _{RRM2}	T _J = 125 °C		-	4.5	8.0			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138			
See fig. 7	Q _{rr2}	T _J = 125 °C		-	124	360			
Peak rate of fall of	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-			
recovery current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	3.5	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	r./ v v			
Weight			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Marking device		Case style TO-263AB (D ² PAK)		HFA08	TB60S				



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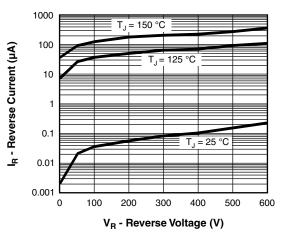


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

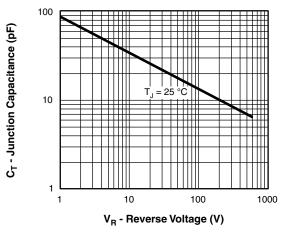
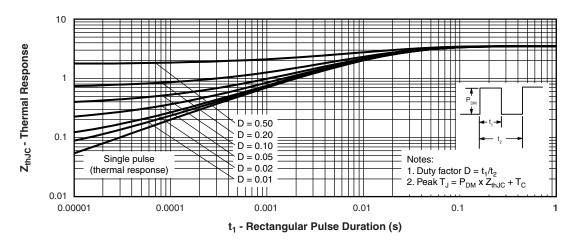
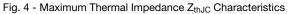


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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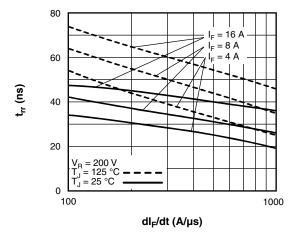


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

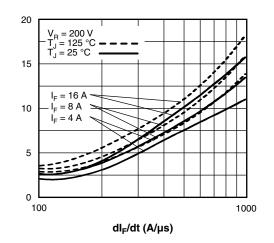


Fig. 6 - Typical Recovery Current vs. dl_F/dt

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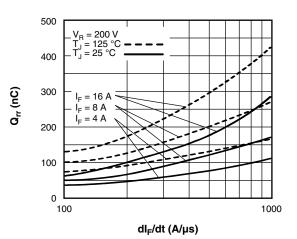


Fig. 7 - Typical Stored Charge vs. dl_F/dt

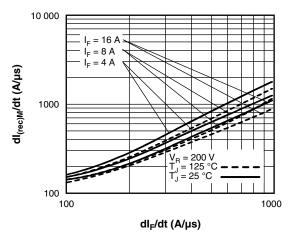


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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I_{rr} (A)

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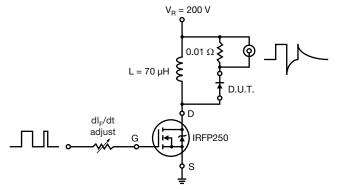
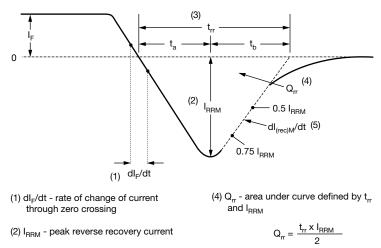


Fig. 9 - Reverse Recovery Parameter Test Circuit



- $\begin{array}{l} (3) \ t_{rr} \ \ reverse \ recovery \ time \ measured \\ from \ zero \ crossing \ point \ of \ negative \\ going \ I_F \ to \ point \ where \ a \ line \ passing \\ through \ 0.75 \ I_{RRM} \ and \ 0.50 \ I_{RRM} \\ extrapolated \ to \ zero \ current. \end{array}$
- (5) $dI_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}
- Fig. 1 Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	08	тв	60	S	TRL	PbF		
		2	3	4	5	6	7	8	9		
	 Vishay Semiconductors product HEXFRED[®] family Process designator: A = electron irradiated Current rating (08 = 8 A) Package outline (TB = TO-220, 2 leads) Voltage rating (60 = 600 V) 										
		- S = D ² PAK									
	9 -	 TRL = tape and reel (left oriented) TRR = tape and reel (right oriented) 									

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA08TB60SPBF	50	1000	Antistatic plastic tube							
VS-HFA08TB60STRRP	800	800	13" diameter reel							
VS-HFA08TB60STRLP	800	800	13" diameter reel							

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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